

# **Device Modeling Report**

COMPONENTS:

DIODE/ GENERAL PURPOSE RECTIFIER/ PROFESSIONAL

PART NUMBER: CMH07

MANUFACTURER: TOSHIBA



**Bee Technologies Inc.**

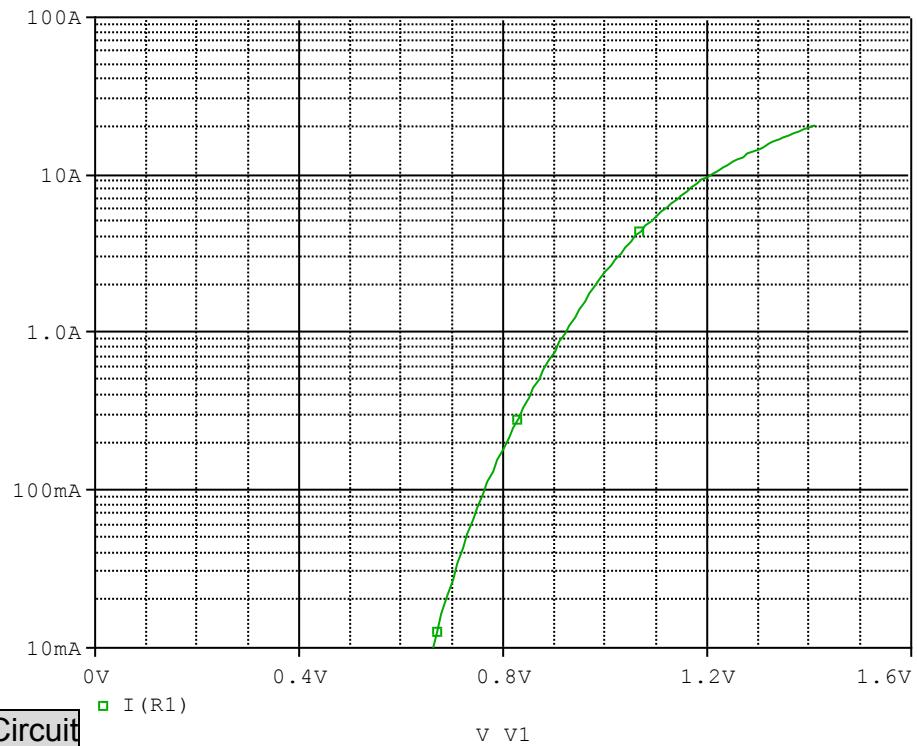
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## DIODE MODEL PARAMETERS

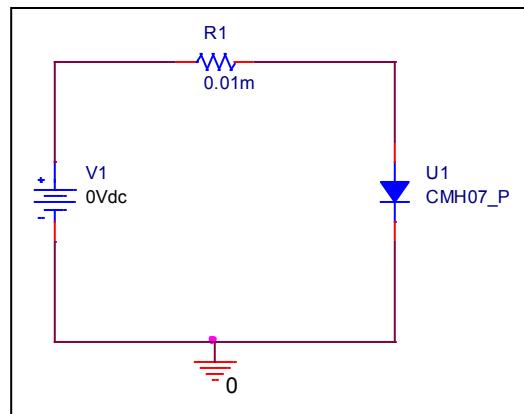
PSpice model parameter	Model description
IS	Saturation Current
N	Emission Coefficient
RS	Series Resistance
IKF	High-injection Knee Current
CJO	Zero-bias Junction Capacitance
M	Junction Grading Coefficient
VJ	Junction Potential
ISR	Recombination Current Saturation Value
BV	Reverse Breakdown Voltage(a positive value)
IBV	Reverse Breakdown Current(a positive value)
TT	Transit Time
EG	Energy-band Gap

## Forward Current Characteristic

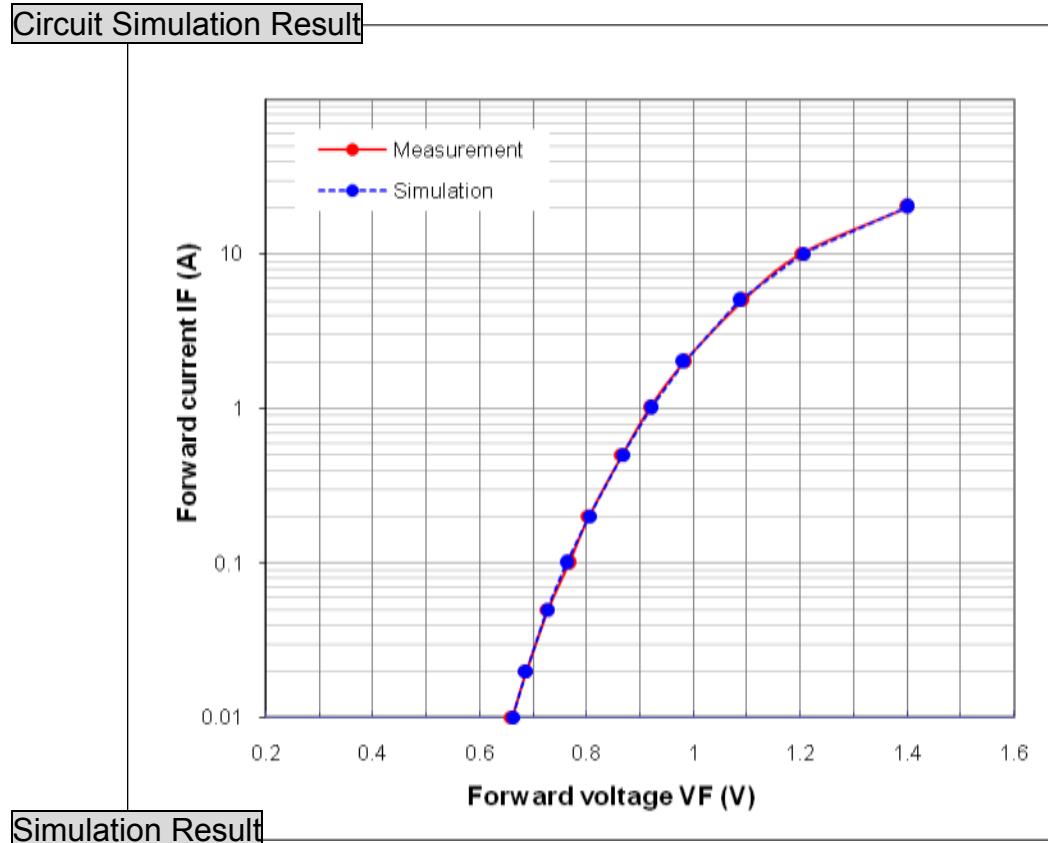
Circuit Simulation Result



Evaluation Circuit



## Comparison Graph

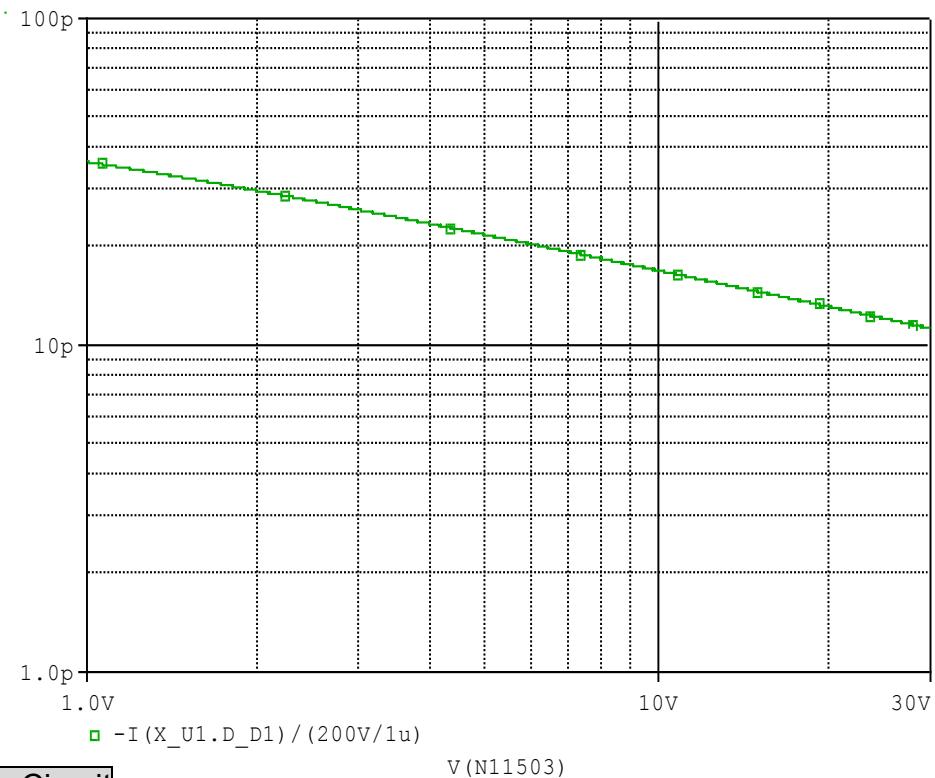


**Simulation Result**

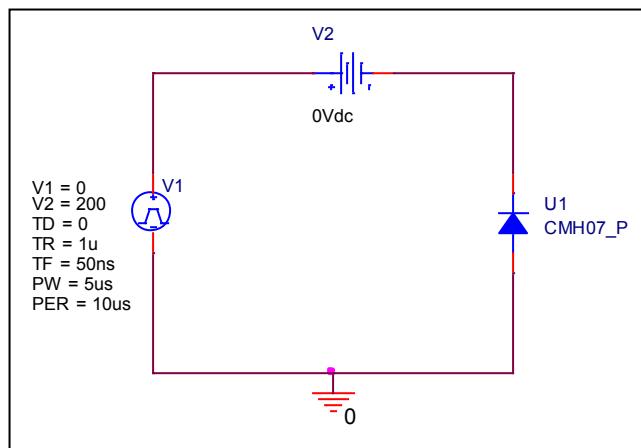
Ifwd (A)	Vfwd (V)		%Error
	Measurement	Simulation	
0.01	0.661	0.662	0.11
0.02	0.687	0.688	0.11
0.05	0.728	0.727	-0.12
0.1	0.768	0.763	-0.60
0.2	0.805	0.806	0.09
0.5	0.867	0.869	0.21
1	0.918	0.921	0.38
2	0.983	0.982	-0.12
5	1.092	1.087	-0.49
10	1.202	1.206	0.36
20	1.401	1.400	-0.05

## Capacitance Characteristic

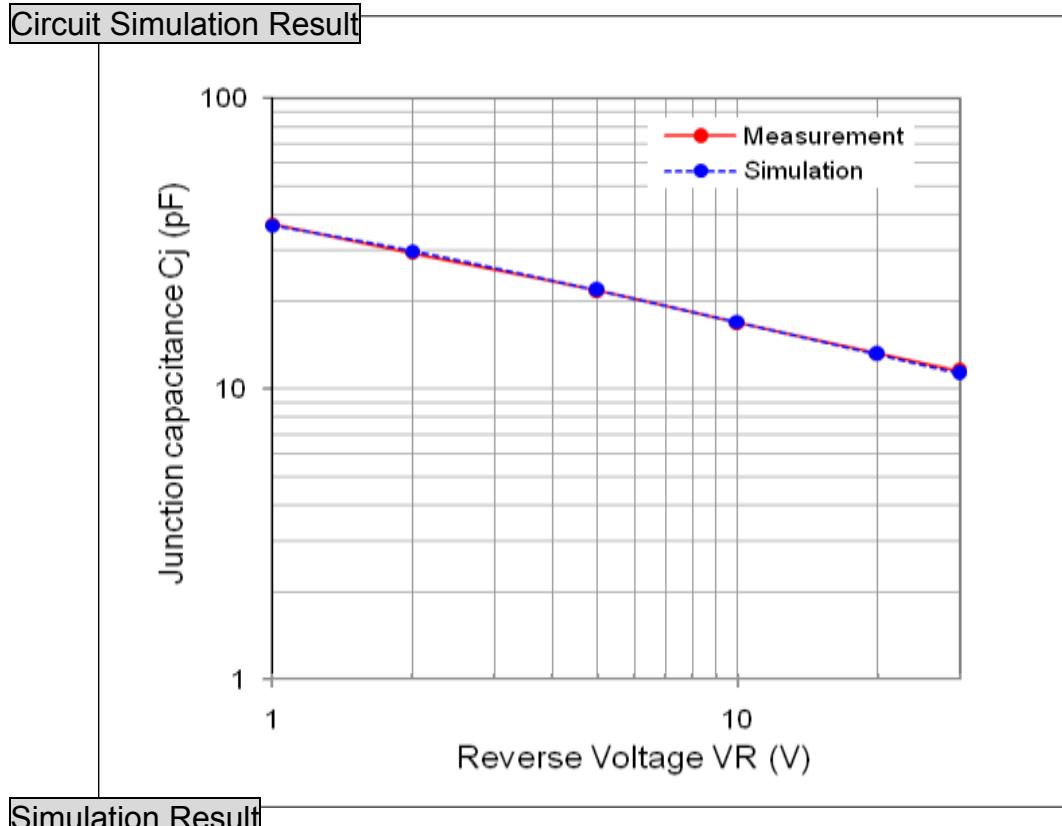
Circuit Simulation Result



Evaluation Circuit



## Comparison Graph

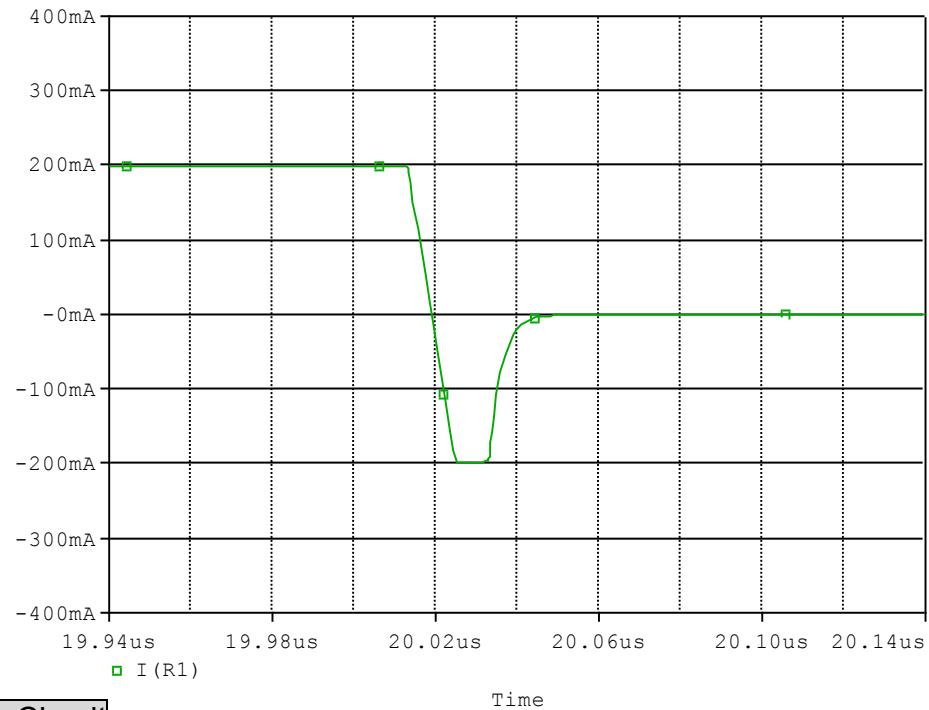


Simulation Result

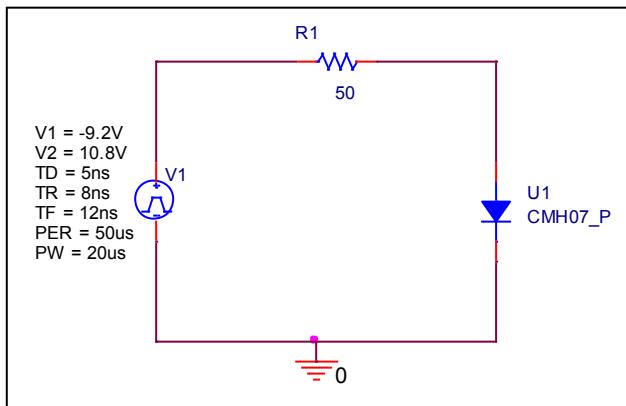
V <sub>rev</sub> (V)	C <sub>j</sub> (pF)		%Error
	Measurement	Simulation	
1	36.700	36.458	-0.66
2	29.300	29.651	1.20
5	21.700	21.755	0.25
10	16.800	16.948	0.88
20	13.200	13.102	-0.74
30	11.500	11.261	-2.08

## Reverse Recovery Characteristic

Circuit Simulation Result



Evaluation Circuit

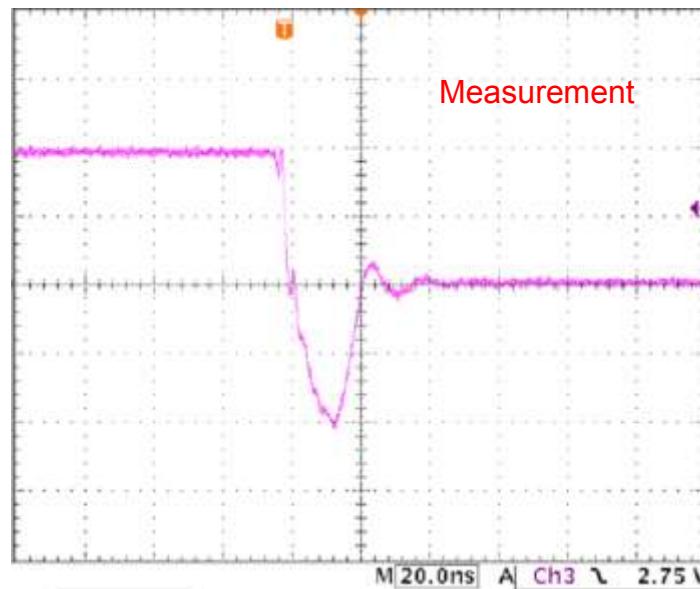


## Compare Measurement vs. Simulation

		Measurement	Simulation	%Error
Trj	ns	<b>13.20</b>	<b>12.86</b>	<b>-2.55</b>
Trb	ns	<b>7.60</b>	<b>7.52</b>	<b>-1.03</b>
Trr	ns	<b>20.80</b>	<b>20.38</b>	<b>-2.00</b>

## Reverse Recovery Characteristic

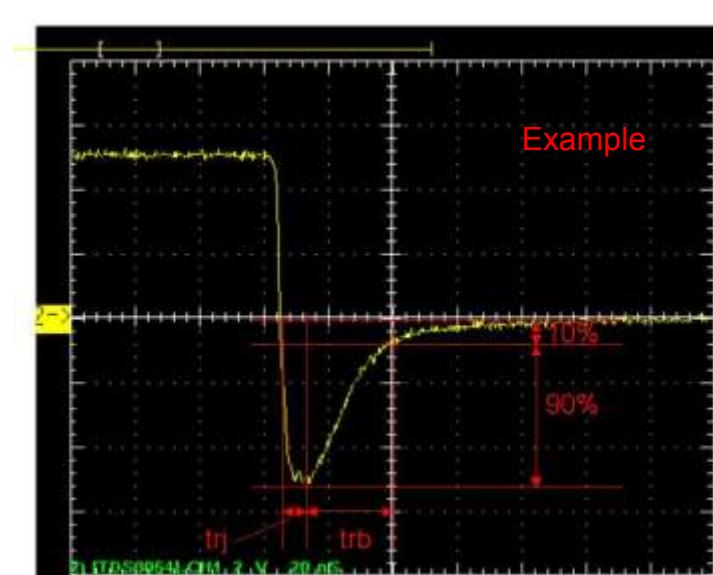
## Reference



Trj = 13.20(ns)

Trb= 7.60 (ns)

Conditions: Ifwd=0.2A,Irev=0.2A, RI=50



Relation between trj and trb